

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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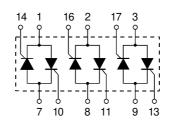


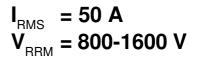


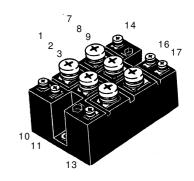
Three Phase AC Controller Modules

Preliminary data

V _{RSM} V _{DSM}	V _{RRM} V _{DRM}	Туре
800	800	VWO 50-08io7
1200	1200	VWO 50-12io7
1400	1400	VWO 50-14io7
1600	1600	VWO 50-16io7







Symbol	Test Conditions	Maximum Ratings		
RMS TRMS	$T_{VI}^{o} = T_{VIM}$	$T_{C} = 85^{\circ}\text{C}$, 50 - 400 Hz (per phase) $T_{VJ} = T_{VJM}$ $T_{C} = 85^{\circ}\text{C}$; (180° sine)		A A A
TAVM I _{TSM}	$T_{VJ} = 45^{\circ}C;$ $V_{B} = 0$	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	520 560	A A
		t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	460 500	A A
l²t	$T_{VJ} = 45^{\circ}C$ $V_{R} = 0$	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	1350 1320	A ² s A ² s
	$T_{VJ} = T_{VJM}$ $V_{R} = 0$	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	1060 1050	A ² s A ² s
(di/dt) _{cr}	$T_{VJ} = T_{VJM}$ $f = 50 \text{ Hz}, t_p = 200$ $V_D = 2/3 V_{DRM}$		100	A/μs
	$I_{G} = 0.3 \text{ A}$ $di_{G}/dt = 0.3 \text{ A}/\mu\text{s}$	non repetitive, $I_T = I_{TAVM}$	500	A/μs
(dv/dt) _{cr}	$T_{VJ} = T_{VJM};$ $R_{GK} = \infty;$ method 1	1000	V/μs	
P _{GM}	$T_{VJ} = T_{VJM}$	t _p = 30 μs	10	W
	$I_{T} = I_{TAVM}$	$t_{p} = 300 \ \mu s$	5	W
P _{GAVM}		•	0.5	W
V _{RGM}			10	V
T _{VJ}			-40+125	°C
T,,			125	°C
T _{stg}			-40+125	°C
V _{ISOL}	50/60 Hz, RMS	t = 1 min	2500	V~
ISUL	$I_{ISOL} \le 1 \text{ mA}$	t = 1 s	3000	V~
M _d		Mounting torque (M5) Terminal connection torque (M3; M5)		Nm/lb.in. Nm/lb.in.
Weight	typ.		180	g

Features

- Thyristor controller for AC (circuit W3C acc. to IEC) for mains frequency
- · Package with metal base plate
- Isolation voltage 3000 V~
- · Planar passivated chips
- UL applied

Applications

- Switching and control of three phase AC circuits
- · Softstart AC motor controller
- Solid state switches
- · Light and temperature control

Advantages

- Easy to mount with two screws
- · Space and weight savings
- Improved temperature and power cycling
- · High power density

Data according to IEC 60747 refer to a single thyristor/diode unless otherwise stated. IXYS reserves the right to change limits, test conditions and dimensions



Symbol	Test Conditions	Characte	eristic \	/alues
I _D , I _R	$T_{VJ} = T_{VJM}; V_{R} = V_{RRM}; V_{D} = V_{DRM}$	≤	5	mA
V _T	I _T = 80 A; T _{VJ} = 25°C	≤	1.65	V
V _{T0}	For power-loss calculations only		0.85	V
r _T			11	mΩ
$\frac{\mathbf{r}_{T}}{\mathbf{V}_{GT}}$	$V_{D} = 6 \text{ V}; \qquad T_{VJ} = 25^{\circ}\text{C}$	≤	1.0	٧
	$T_{VJ}^{O} = -40^{\circ}C$	\leq	1.6	V
l _{gt}	$V_{D} = 6 \text{ V}; \qquad T_{VJ}^{\circ} = 25^{\circ}\text{C}$	≤	100	mΑ
	$T_{VJ} = -40^{\circ}C$	≤	150	mA
$V_{_{\mathrm{GD}}}$	$T_{V,I} = T_{V,IM}$; $V_D = 2/3 V_{DBM}$	≤	0.2	V
I _{GD}	A2 A2W	\leq	5	mA
I _L	T _{v,i} = 25°C; t _P = 10 μs	<u>≤</u>	200	mA
	$I_{\rm G} = 0.3 \text{ A}; di_{\rm G}/dt = 0.3 \text{A}/\mu\text{s}$			
I _H	$T_{VJ} = 25^{\circ}C; V_{D} = 6 V; R_{GK} = \infty$	≤	150	mA
\mathbf{t}_{gd}	$T_{VJ} = 25^{\circ}C; V_{D} = 1/2 V_{DRM}$	≤	2	μS
	$I_{\rm G} = 0.3 \text{ A}; di_{\rm G}/dt = 0.3 \text{A}/\mu\text{s}$			
t _q	$T_{VJ} = T_{VJM}$; $I_T = 20 \text{ A}$, $t_P = 200 \mu\text{s}$; $di/dt = -10 \text{ A}/\mu$	ıs typ.	150	μS
	$V_{R} = 100 \text{ V}; \text{ dv/dt} = 15 \text{ V/}\mu\text{s}; V_{D} = 2/3 \text{ V}_{DRM}$			
R_{thJC}	per thyristor; sine 180°el		1.20	K/W
1100	per module		0.20	K/W
R_{thJK}	per thyristor; sine 180°el		1.31	K/W
	per module		0.218	K/W
d _s	Creeping distance on surface	·	8.0	mm
d _A	Creepage distance in air		4.5	mm
a	Max. allowable acceleration		50	m/s ²

Dimensions in mm (1 mm = 0.0394")

